

Method for producing a semiconductor substrate having an epitaxially deposited layer

Abstract

The invention relates to a method for producing a semiconductor substrate having an epitaxially deposited layer, comprising the following successive steps: - etching (ETCH) a susceptor of an epitaxy reactor; - coating (COAT) the susceptor; - placing a semiconductor substrate on the susceptor; - depositing (EPI) an epitaxial layer on the semiconductor substrate. The method also comprises, after coating and before deposition, exposing (ISO) the susceptor to an oxygen-containing gas mixture. The method further comprises, after placement and before deposition, a baking step (BAKE) involving baking the semiconductor substrate, which, except on the underside of the semiconductor substrate, removes an oxide layer formed by exposing the susceptor to an oxygen-containing gas mixture.

Fig. 2